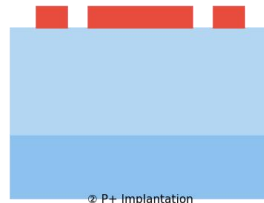


科创作业 4



① Full Epitaxial Structure



② P+ Implantation (Anode + Guard Rings)



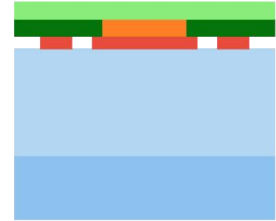
③ Thermal Oxidation + SiO₂ Deposition



④ Etch Contact Windows



⑤ Front Metal 1 (Ti/Al/Ti/Ni)



⑥ Passivation Layer Deposition



⑦ Etch PAD Windows

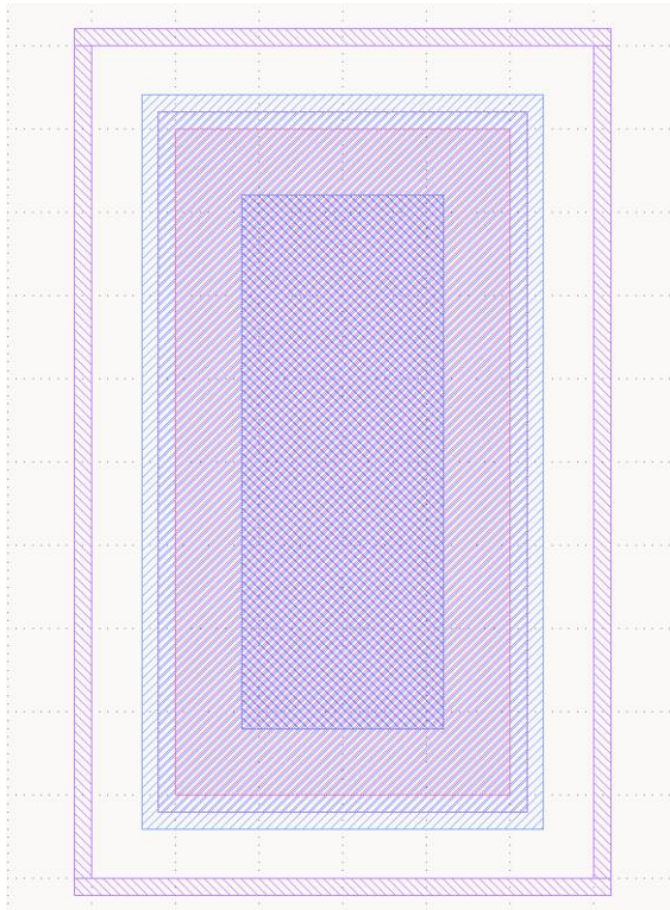


⑧ Front Metal 2 & Field Plate



⑨ Substrate Thinning + Backside Metal

1.



2.